

# Effects of ZnMgO Electron Transport Layer on the Performance of InP-Based Inverted Quantum Dot Light-Emitting Diodes

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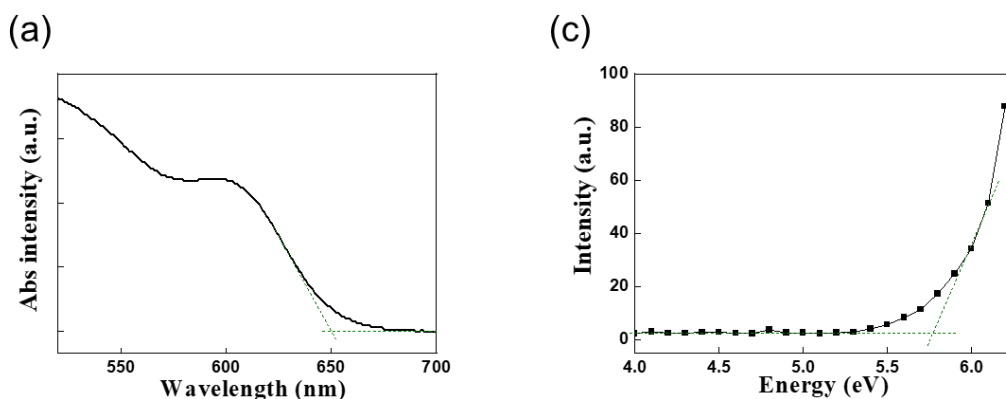


Figure S1. (a) UV-visible spectra of InP QDs, and the calculated  $E_g$  value is 1.9 eV; (b) UPS spectra of InP QDs, and the calculated HOMO and LUMO value is 5.8 eV and 3.9 eV, respectively.